FAIRCHILD SEMICONDUCTOR®

November 2007

UniFET™

FDP7N50F / FDPF7N50F

N-Channel MOSFET, FRFET

500V, 6A, 1.15Ω

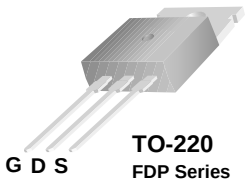
Features

- $R_{DS(on)}$ = 0.95Ω (Typ.)@ V_{GS} = 10V, I_D = 3A
- Low gate charge (Typ. 15nC)
- Low C_{rss} (Typ. 6.3pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant

Description

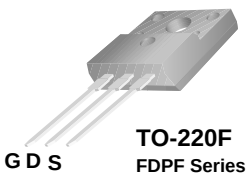
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advance technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.



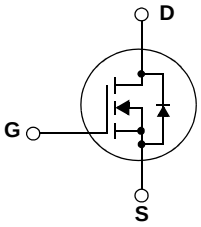
G D S

TO-220
FDP Series



G D S

TO-220F
FDPF Series



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter		FDP7N50F	FDPF7N50F	Units
V_{DSS}	Drain to Source Voltage		500		V
V_{GSS}	Gate to Source Voltage		±30		V
I_D	Drain Current	-Continuous (T_C = 25°C)	6	6*	A
		-Continuous (T_C = 100°C)	3.6	3.6*	
I_{DM}	Drain Current	- Pulsed (Note 1)	24	24*	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	270		mJ
I_{AR}	Avalanche Current	(Note 1)	6		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	20		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation	(T_C = 25°C)	200	38.5	W
		- Derate above 25°C	1.59	0.3	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300		°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP7N50F	FDPF7N50F	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.4	4.0	°C/W
$R_{\theta CS}$	Thermal Resistance, Junction to Ambient	0.5	-	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP7N50F	FDP7N50F	TO-220	-	-	50
FDPF7N50F	FDPF7N50F	TO-220F	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, T_J = 25°C	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.5	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500V, V_{GS} = 0V	-	-	10	μA
		V_{DS} = 400V, T_C = 125°C	-	-	100	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 3A	-	0.95	1.15	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D = 3A (Note 4)	-	4.3	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	720	960	pF
C_{oss}	Output Capacitance		-	85	115	pF
C_{rss}	Reverse Transfer Capacitance		-	6.3	10	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 400V, I_D = 6A, V_{GS} = 10V (Note 4, 5)	-	15	20	nC
Q_{gs}	Gate to Source Gate Charge		-	4.5	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 250V, I_D = 6A, R_G = 25Ω (Note 4, 5)	-	17	45	ns
t_r	Turn-On Rise Time		-	30	70	ns
$t_{d(off)}$	Turn-Off Delay Time		-	35	80	ns
t_f	Turn-Off Fall Time		-	20	50	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	24	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 6A	-	-	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 6A, dI_F/dt = 100A/μs (Note 4)	-	85	-	ns
Q_{rr}	Reverse Recovery Charge		-	0.15	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 13mH, I_{AS} = 6A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 6A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

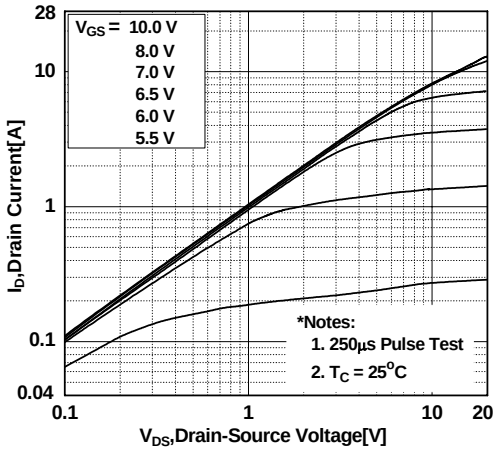


Figure 2. Transfer Characteristics

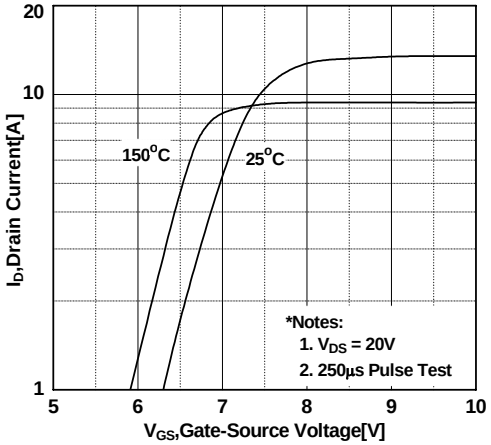


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

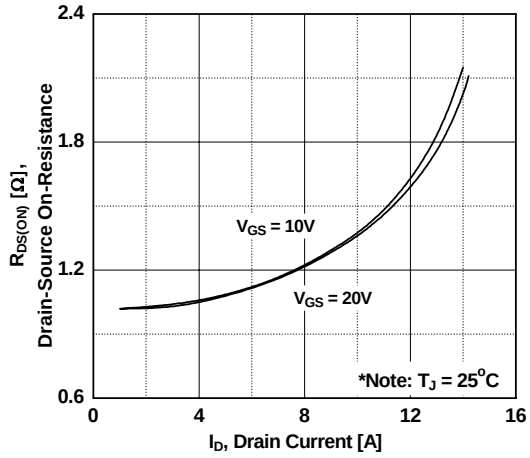


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

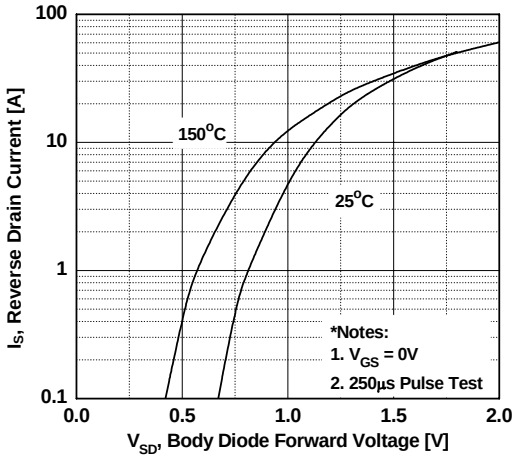


Figure 5. Capacitance Characteristics

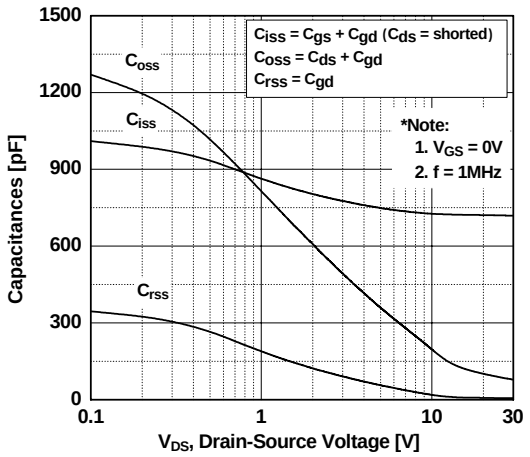
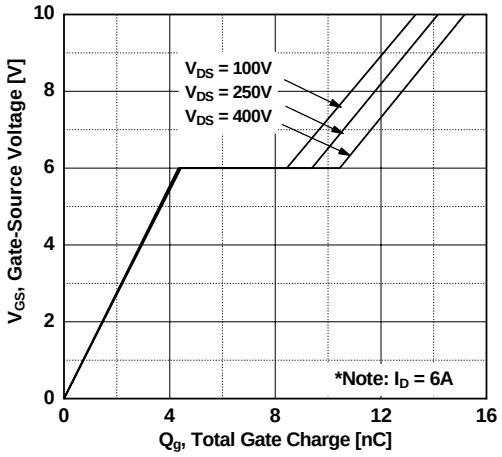


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

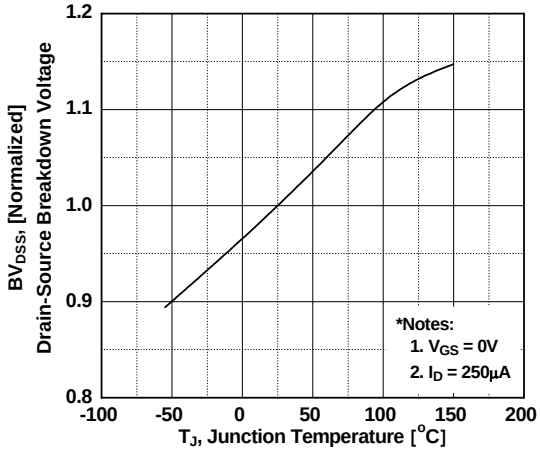


Figure 8. Maximum Safe Operating Area - FDPF7N50F

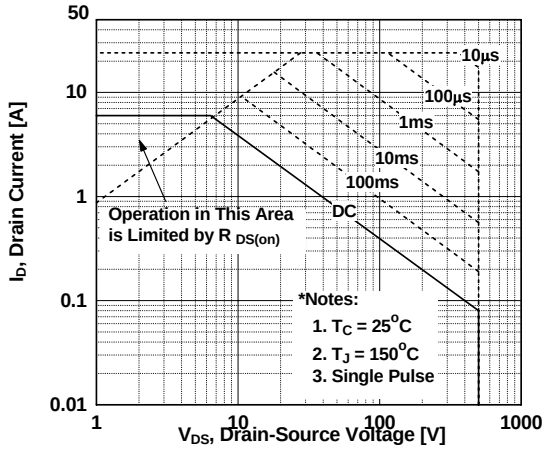


Figure 9. Maximum Drain Current vs. Case Temperature - FDPF7N50F

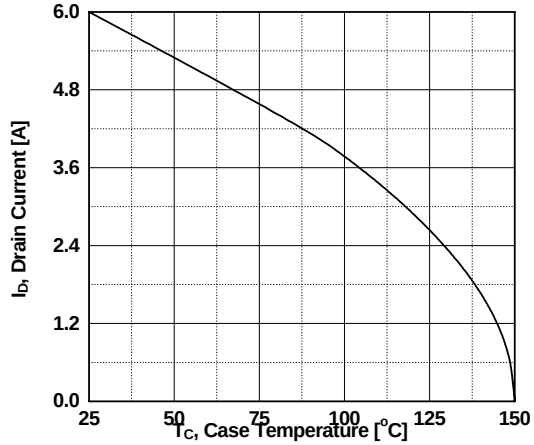
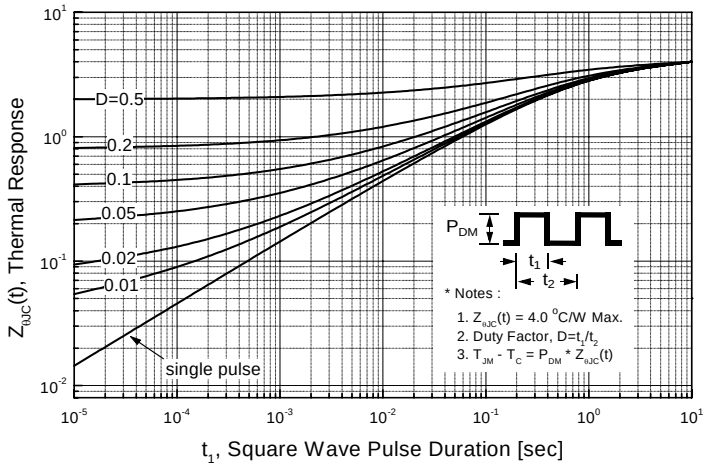
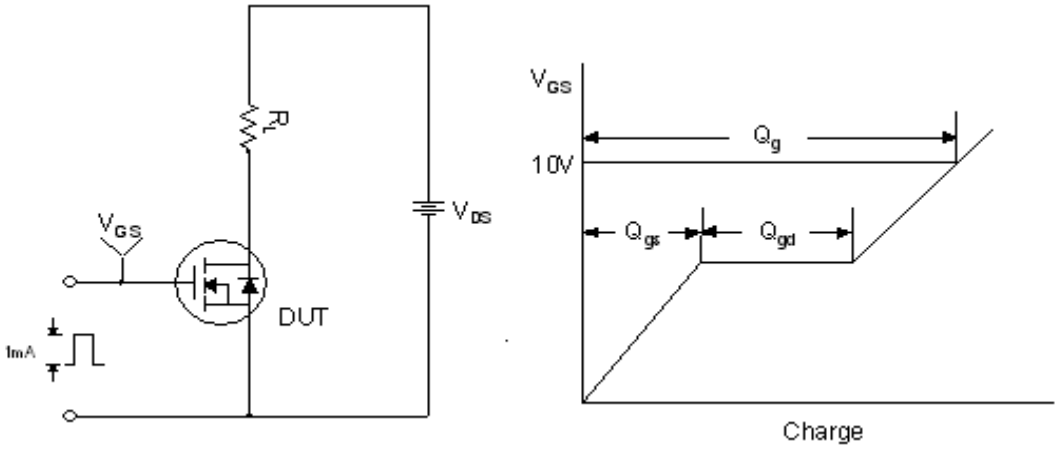


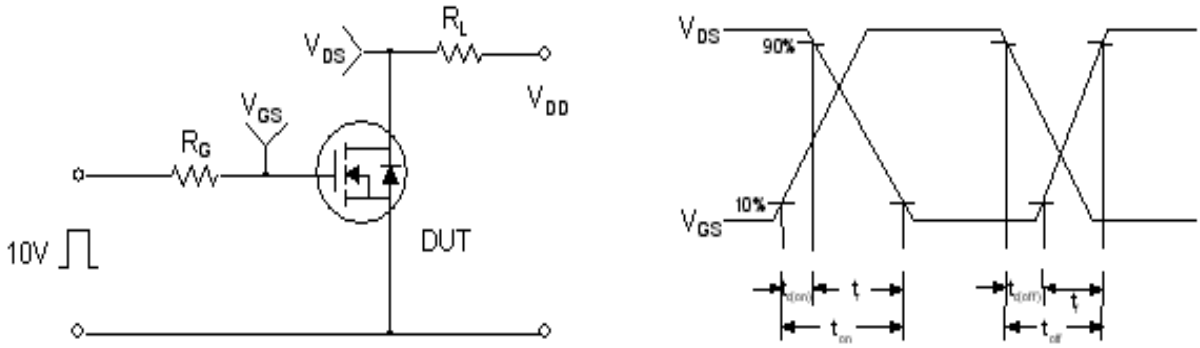
Figure 10. Transient Thermal Response Curve - FDPF7N50F



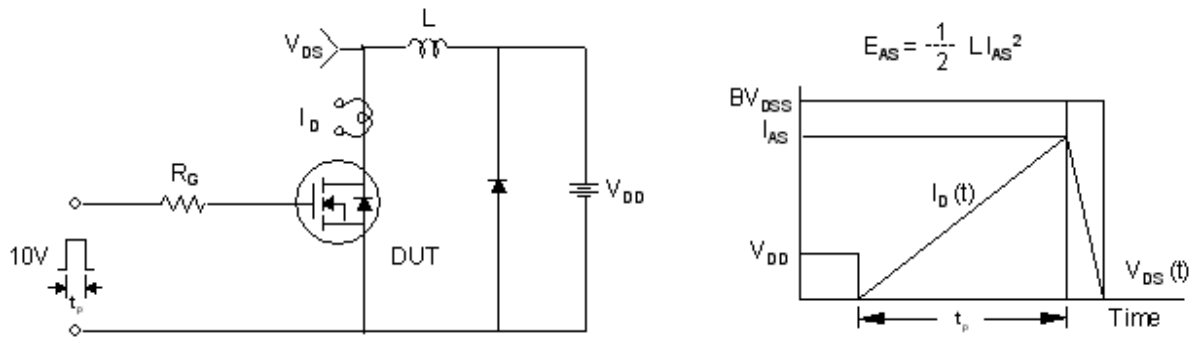
Gate Charge Test Circuit & Waveform



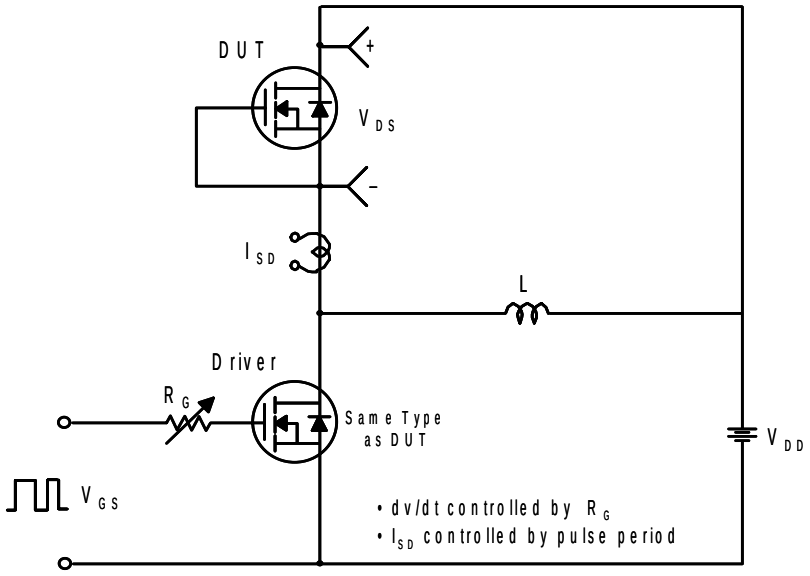
Resistive Switching Test Circuit & Waveforms

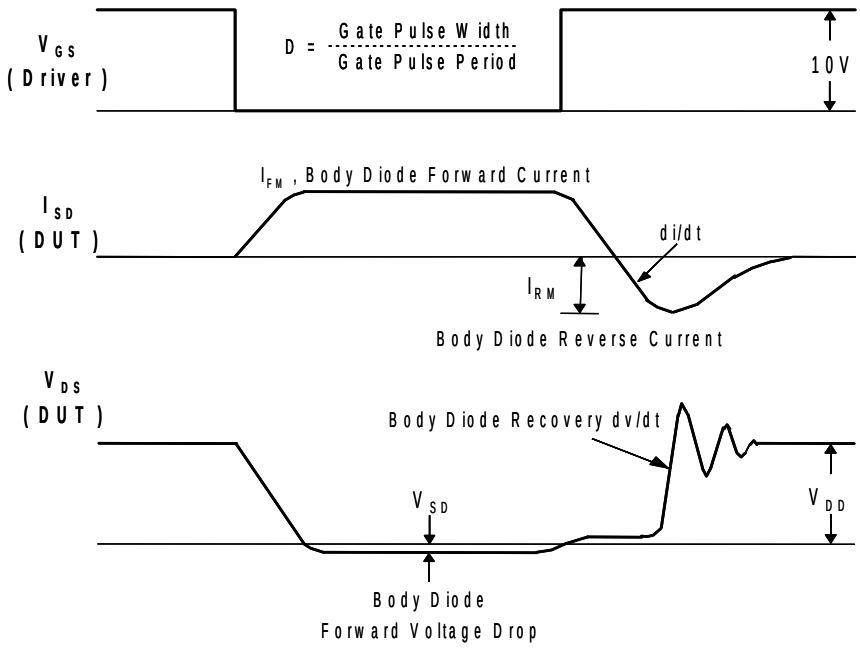


Unclamped Inductive Switching Test Circuit & Waveforms



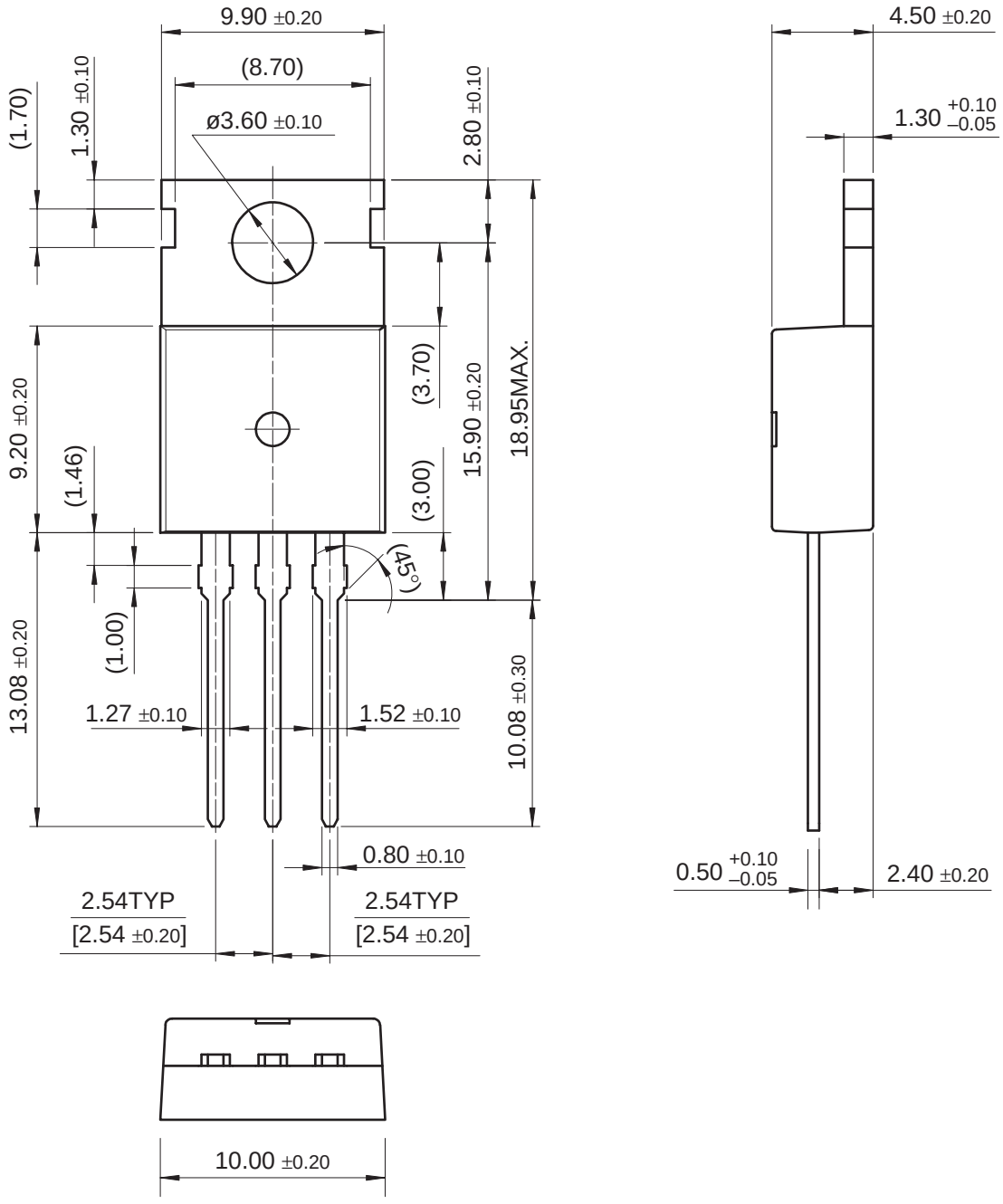
Peak Diode Recovery dv/dt Test Circuit & Waveforms





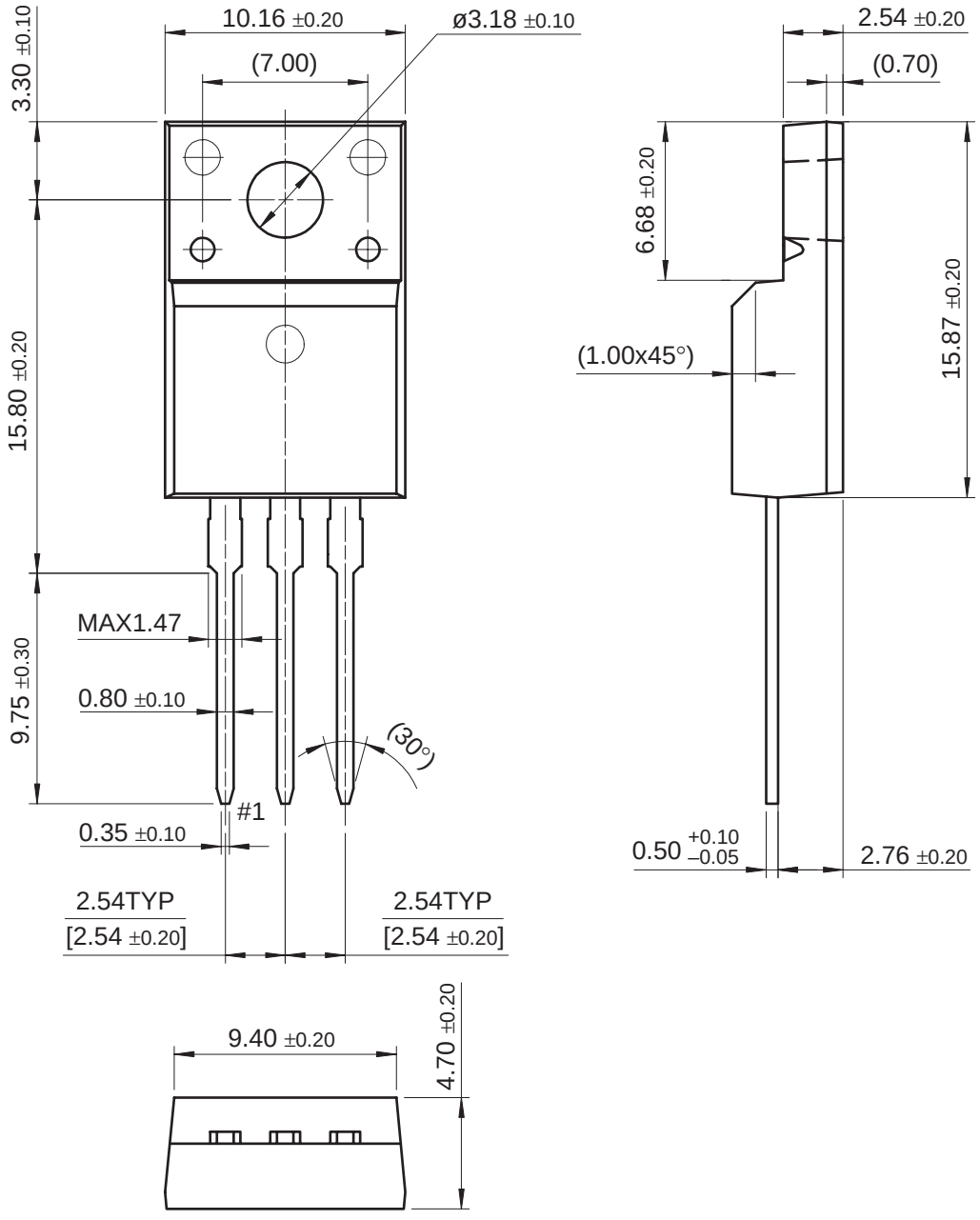
Mechanical Dimensions

TO-220



Mechanical Dimensions

TO-220F



Dimensions in Millimeters

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx®	Green FPS™	Power247®	SuperSOT™-8
Build it Now™	Green FPS™ e-Series™	POWEREDGE®	SyncFET™
CorePLUS™	GTO™	Power-SPM™	The Power Franchise®
CROSSVOLT™	*i-Lo*™	PowerTrench®	the power franchise
CTL™	IntelliMAX™	Programmable Active Droop™	TinyBoost™
Current Transfer Logic™	ISOPLANAR™	QFET®	TinyBuck™
EcoSPARK®	MegaBuck™	QS™	TinyLogic®
F®	MICROCOUPLER™	QT Optoelectronics™	TINYOPTO™
Fairchild®	MicroFET™	Quiet Series™	TinyPower™
Fairchild Semiconductor®	MicroPak™	RapidConfigure™	TinyPWM™
FACT Quiet Series™	MillerDrive™	SMART START™	TinyWire™
FACT®	Motion-SPM™	SPM®	µSerDes™
FAST®	OPTOLOGIC®	STEALTH™	UHC®
FastvCore™	OPTOPLANAR®	SuperFET™	UniFET™
FPS™	®	SuperSOT™-3	VCX™
FRFET®	PDP-SPM™	SuperSOT™-6	
Global Power Resource℠	Power220®		

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.

Rev. I31